

EAST - [Untitled1:1]

File View Edit Tools Window Help

Drafts
Pending
Active
 L1: (16) "5898186"
 L2: (9) "5994915"
 L3: (762) (stress\$3 near2 test\$3) and leakage
 L4: (138) (stress\$3 near2 test\$3) same leakage
 L5: (42) (stress\$3 near2 test\$3) with leakage
 L6: (97144) 4 and common global
 L8: (2) 7 and (single adj clip)
 L7: (77) 4 and (common global)
Failed
Saved
Favorites
Tagged (0)

DBs: USPAT; US-PGPUB; EPO; JPO
 Default operator: OR
☐ Pure:
☐ Highlight all hit terms initially

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	16	"5898186"	USPAT; US-PGPUB; EPO; JPO
2	BRS	L2	9	"5994915"	USPAT; US-PGPUB; EPO; JPO
3	BRS	L3	762	(stress\$3 near2 test\$3) and leakage	USPAT; US-PGPUB; EPO; JPO
4	BRS	L4	138	(stress\$3 near2 test\$3) same leakage	USPAT; US-PGPUB; EPO; JPO
5	BRS	L5	42	(stress\$3 near2 test\$3) with leakage	USPAT; US-PGPUB; EPO; JPO
6	BRS	L6	97144	4 and common global	USPAT; US-PGPUB; EPO; JPO
7	BRS	L8	2	7 and (single adj clip)	USPAT; US-PGPUB; EPO; JPO
8	BRS	L7	77	4 and (common global)	USPAT; US-PGPUB; EPO; JPO

Ready

EAST - [Untitled1:1]

FileViewEditToolsWindowHelp

Drafts

Pending

Active

L1: (0) memory same (global adj (wordline word-l

L2: (2) memory and (global adj (wordline word-lir

Failed

Saved

Favorites

Tagged (0)

UDC

Queue

Trash

Query

DBs

USPAT; US-PGPUB; EPO; JPO

Default operator

OR

Plurals

Highlight all hit terms in body

1BRS hits2BRS hitsImageTextHTML

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	memory same (global adj (wordline word-line word)) same (global adj (bitline bit-line bit)) same test\$3 same (conductive conductor conducting)	USPAT; US-PGPUB; EPO; JPO
2	BRS	L2	2	memory and (global adj (wordline word-line word)) and (global adj (bitline bit-line bit)) and test\$3 and (conductive conductor conducting)	USPAT; US-PGPUB; EPO; JPO

DetailsImageText

Ready

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EAST - [Untitled1:1]

File View Edit Tools Window Help

DBs: USPAT:US-PGPUB:EPO:JPO

Default operator: OR

Purels: ☐ Highlight all hit items initially

Pending

Active

- L1: (2) test\$3 same (common adj (wordline word-line word)) same (common adj (bitline bit-line bit)) same cell
- L2: (102) test\$3 and (common adj (wordline word-line word)) and (common adj (bitline bit-line bit)) and cell
- L3: (77) 2 and connect\$3 and together
- L4: (18) 3 and (single adj cell)
- L5: (1) (conduc\$3 adj line) with test\$3 with leak
- L6: (0) memory with (conduc\$3 adj line) with test\$3 with leakage
- L7: (0) memory same (conduc\$3 adj line) same test\$3 same leakage
- L8: (1) memory and ((conduc\$3 adj line) same test\$3 same leakage)
- L9: (0) (memory adj cell) and ((conduc\$3 adj line) same test\$3 same leakage)
- L10: (19) (memory adj cell) and (conduc\$3 adj line) and test\$3 and leakage and current

Failed

Saved

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2	test\$3 same (common adj (wordline word-line word)) same (common adj (bitline bit-line bit)) same cell	USPAT: US-PGPUB; EPO: JPO
2	BRS	L2	102	test\$3 and (common adj (wordline word-line word)) and (common adj (bitline bit-line bit)) and cell	USPAT: US-PGPUB; EPO: JPO
3	BRS	L3	77	2 and connect\$3 and together	USPAT: US-PGPUB; EPO: JPO
4	BRS	L4	18	3 and (single adj cell)	USPAT: US-PGPUB; EPO: JPO
5	BRS	L5	1	(conduc\$3 adj line) with test\$3 with leakage	USPAT: US-PGPUB; EPO: JPO
6	BRS	L6	0	memory with (conduc\$3 adj line) with test\$3 with leakage	USPAT: US-PGPUB; EPO: JPO
7	BRS	L7	0	memory same (conduc\$3 adj line) same test\$3 same leakage	USPAT: US-PGPUB; EPO: JPO
8	BRS	L8	1	memory and ((conduc\$3 adj line) same test\$3 same leakage)	USPAT: US-PGPUB; EPO: JPO
9	BRS	L9	0	(memory adj cell) and ((conduc\$3 adj line) same test\$3 same leakage)	USPAT: US-PGPUB; EPO: JPO
10	BRS	L10	19	(memory adj cell) and (conduc\$3 adj line) and test\$3 and leakage and current	USPAT: US-PGPUB; EPO: JPO

Ready

NUM

EAST - [Untitled1:1]

File View Edit Tools Window Help

Drafts
Pending
Active
L1: (0) test\$3 same array same bist same dice same wafer same common same together
L2: (5) test\$3 and array and bist and dice and wafer and common and together
L3: (3368) circuit with (test\$3 detect\$3) with leakage
L4: (4) circuit with (test\$3 detect\$3) with leakage with sram
L5: (41) circuit same (test\$3 detect\$3) same leakage same sram
Failed
Saved
Favorites
Tagged (0)
UDC
Queue

DBs: USPAT; US-PGPUB; EPO; JPO
Default operator: OR
Plural: Highlight all hit items initially

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	test\$3 same array same bist same dice same wafer same common same together	USPAT; US-PGPUB; EPO; JPO
2	BRS	L2	5	test\$3 and array and bist and dice and wafer and common and together	USPAT; US-PGPUB; EPO; JPO
3	BRS	L3	3368	circuit with (test\$3 detect\$3) with leakage	USPAT; US-PGPUB; EPO; JPO
4	BRS	L4	4	circuit with (test\$3 detect\$3) with leakage with sram	USPAT; US-PGPUB; EPO; JPO
5	BRS	L5	41	circuit same (test\$3 detect\$3) same leakage same sram	USPAT; US-PGPUB; EPO; JPO

Ready

NUM

EAST - [Untitled1:1]

File View Edit Tools Window Help

L6: (6568) test\$3 and structure and leakage and
L7: (1427) 6 and complement
L8: (325) 7 and (single adj cell)
L9: (220) 8 and pad
L10: (214) 9 and measur\$3
L11: (214) 10 and element
L12: (203) 11 and average
L14: (201) 12 and substrate
L16: (1) 14 and join
Failed
Saved

DB: USPAT:US-PGPUB:EPO:JPO
Default operator: OR
☐ Exact
☐ Highlight all hit items initially

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	51	ram and test\$3 and measur\$3 and (current adj leakage) and common and conduct\$3 and line	USPAT: US-PGPUB; EPO: JPO
2	BRS	L2	0	(array with cell) same (connect\$3 with together with comunon) same conduct\$3 same (single adj cell)	USPAT: US-PGPUB; EPO: JPO
3	BRS	L3	83	(array with cell) and (connect\$3 with together with comunon) and conduct\$3 and (single adj cell)	USPAT: US-PGPUB; EPO: JPO
4	BRS	L4	32	3 and leakage	USPAT: US-PGPUB; EPO: JPO
5	BRS	L5	12	4 and test\$3	USPAT: US-PGPUB; EPO: JPO
6	BRS	L6	6568	test\$3 and structure and leakage and current and common and connect\$3 and together and conduct\$3	USPAT: US-PGPUB; EPO: JPO
7	BRS	L7	1427	6 and complement	USPAT: US-PGPUB; EPO: JPO
8	BRS	L8	325	7 and (single adj cell)	USPAT: US-PGPUB; EPO: JPO
9	BRS	L9	220	8 and pad	USPAT: US-PGPUB; EPO: JPO
10	BRS	L10	214	9 and measur\$3	USPAT: US-PGPUB; EPO: JPO
11	BRS	L11	214	10 and element	USPAT: US-PGPUB; EPO: JPO
12	BRS	L12	203	11 and average	USPAT: US-PGPUB; EPO: JPO
13	BRS	L14	201	12 and substrate	USPAT: US-PGPUB; EPO: JPO
14	BRS	L16	1	14 and join	USPAT: US-PGPUB; EPO: JPO

Ready

EAST - [Untitled1:1]

File View Edit Tools Window Help

Drafts
Pending
Active
L2: (0) (test\$3 adj structure) same array same cell s
L3: (23) (test\$3 adj structure) and array and cell an
Failed
Saved
Favorites
Tagged (0)
UDC
Queue
Trash

DBs: USPAT, US-PGPUB, EPO, JPO
Default operator: OR
P: Highlight all hit terms initially

	Type	L #	Hits	Search Text	DBs
1	BRS	L2	0	(test\$3 adj structure) same array same cell same (conduct\$3 adj line) same together same common	USPAT, US-PGPUB, EPO, JPO
2	BRS	L3	23	(test\$3 adj structure) and array and cell and (conduct\$3 adj line) and together and common	USPAT, US-PGPUB, EPO, JPO

Ready

NUM

EAST - [default1.wsp:1]

File View Edit Tools Window Help

Drafts
 Pending
 Active
 L1: (2) sram and test\$3 and
 Failed
 Saved
 Favorites
 Tagged (0)
 UDC
 Queue
 Trash

Search Edit Browse Queue Clear

DBs: USPAT; US-PGPUB; EPD; JPO ☒ Plurals
 Default operator: OR ☒ Highlight all hit terms initial

BRS 1... IS&R ... Image Text HTML

	Type	L #	Hits	Search Text	DBs	Time S
1	BRS	L1	2	sram and test\$3 and measur\$3 and (current adj leakage) and common and conductive and line and pad	USPAT ; US-PG PUB;	2003/04/19

Start [Progress Bar] 1:40 PM

EAST - [default1.wsp:1]

File View Edit Tools Window Help

Drafts
Pending
Active
L1: (1022) sram and current
L2: (106) sram and (current
L3: (42) 2 and test\$3 and
L4: (7) 3 and common and 1
Failed
Saved
Favorites
Tagged (1)
UDC

Search List Browse Queue Clear
DBs: USPAT;US-PGPUB;EPO;JPO
Default operator: OR
Plurals
Highlight all hit terms initial

BRS f... I&R... Image Text HTML

	Type	L #	Hits	Search Text	DBs	Time S
1	BRS	L1	1022	sram and current and leakage and measur\$3	USPAT ; US-PG	2003/04/19
2	BRS	L2	106	sram and (current adj leakage) and measur\$3	USPAT ; US-PG	2003/04/19
3	BRS	L3	42	2 and test\$3 and structure	USPAT ; US-PG	2003/04/19
4	BRS	L4	7	3 and common and line and pad	USPAT ; US-PG	2003/04/19

Start [Icons] 11:14 AM

The screenshot shows the EAST search application window titled "EAST - [default1.wsp:1]". The interface includes a menu bar (File, View, Edit, Tools, Window, Help), a toolbar, and a left sidebar with a tree view containing folders like Drafts, Pending, Active, Failed, Saved, Favorites, Tagged (0), UDC, Queue, and Trash. The main area displays search controls at the top (Search, List, Browse, Queue, Clear buttons; QBs field set to "USPAT:US-PGPUB:EPO:JPD"; Plurals and Highlight all hit terms initial checkboxes) and a search result preview below ("sram and test\$3 and measur\$3 and (current adj leakage) and common and conductive and line and pad"). A bottom toolbar contains icons for BRS, IS&R, Image, Text, and HTML.

	U	L	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030032292 A1	20030213	62	Fabrication method of semiconductor integrated	438/692	438/690
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5255230 A	19931019	10	Method and apparatus for testing the continuity of	365/201	365/190; 365/203;

EAST - [default1.wsp.1]

File View Edit Tools Window Help

Drafts
Pending
Active

- L1: (1022) sram and current
- L2: (106) sram and (current
- L3: (42) 2 and test\$3 and
- L4: (7) 3 and common and 1

Failed
Saved
Favorites
Tagged (1)
UDC

Search List Browse Queue Clear

DBs: USPAT:US-PGPUB:EPO:JPO ☒ Plurals ☒ Highlight all hit terms initial

Default operator: OR

3 and common and line and pad

BRS I... IS&R... Image Text HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030052371 A1	20030320	66	Semiconductor integrated circuit device	257/371	257/288; 257/368;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030032292 A1	20030213	62	Fabrication method of semiconductor integrated	438/692	438/690
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20010034093 A1	20011025	66	Semiconductor integrated circuit device	438/199	257/E27.06; 257/E27.061;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6500715 B2	20021231	62	Method of forming a CMOS structure having gate	438/275	257/E21.623; 257/E21.626;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6307236 B1	20011023	63	Semiconductor integrated circuit device	257/392	257/402; 257/406;
6	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6119250 A	20000912	32	Semiconductor integrated circuit	714/718	365/201
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5844416 A	19981201	12	Ion-beam apparatus and method for analyzing and	324/750	

Start [Icons] 11:13 AM